## RULES

This is a closed book, closed notes test. You are, however, allowed one one piece of paper (front side only) for notes and definitions, but no sample problems. You must staple your equations sheet to the back of your test when you hand your test in.

You are permitted to use a calculator.

You have 50 minutes to complete the test. Please read through the entire test before starting, and read through the directions carefully. To receive partial credit, you must show your work.

There is to be absolutely no cheating. Cheating will not be tolerated.

I you have any questions, please raise your hand, and I will come to you to answer them. Do not hesitate to ask questions.

$$\begin{array}{c} n_i \!\!=\!\! 10^{10} cm^{\text{--}3}\!, \; \mu_n \!\!=\!\! 1360 cm^2 / V s, \; \mu_p \!\!=\!\! 460 cm^2 / V s, \; \tau_n \!\!=\!\! \tau_p \!\!=\!\! 100 \mu s, \; E_g \!\!=\!\! 1.12 eV, \\ K_s \!\!=\!\! 11.8, \; \epsilon_0 \!\!=\!\! 8.854 x 10^{\text{--}12} F / m, \\ k \!\!=\!\! 1.38 x 10^{\text{--}23} J / K, \; T \!\!=\!\! 300 K, \; q \!\!=\!\! 1.602 x 10^{\text{--}19} C \end{array}$$

Opamp Parameters Vsat=±15V

Diode Parameters  $V_{ON}=0.7$ ,  $V_Z=5.6V$ , n=1,  $I_0=0.1pA$ 

| Problem | Value | Score |
|---------|-------|-------|
| 1       | 10    |       |
| 2       | 10    |       |
| 3       | 20    |       |
| 4       | 15    |       |
| 5       | 20    |       |
| 6       | 20    |       |
| 7       | 5     |       |
| Total   | 100   |       |

| EE 355 | Analog | Electronics |
|--------|--------|-------------|
| Test 1 |        |             |

Name Solutions
February 22, 2016

## PROBLEM 1

(10 Points)

Fill in the blank with the most appropriate response.

An ideal voltage-controlled voltage source has \_\_\_\_\_\_infinite \_\_\_\_\_\_input impedance and \_\_\_\_\_\_output impedance.

is a type of thermal motion of charged particles due to a concentration gradient.

Silicon has \_\_\_\_\_\_ valence band electrons (i.e. outer shell electrons).

A/An Acceptor is a type of dopant that is used to create p-type material in silicon.

## PROBLEM 2

(10 Points)

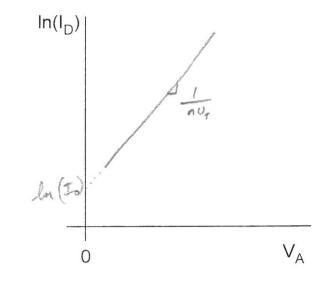
Draw the following.

- A. General band diagram of n-type material (make sure that you label all bands).
- B. The <u>forward bias</u> current in a p-n junction on the axes that have been provided. Be sure to <u>label</u> any slopes, intercepts, or significant items.

Band Diagram (n-type)

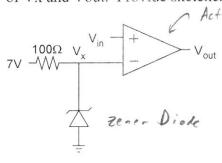
Diode Current (Forward Bias)

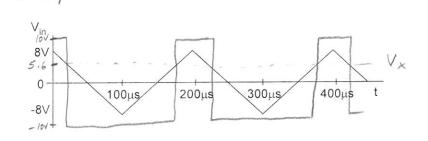
Ex



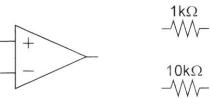
(20 Points)

For the following circuit, the input signal is displayed below. Determine the time-domain values of Vx and Vout. Provide sketches of these signals. Acts as a Comperator





With the following three circuit components, design an amplifier with the highest possible |gain| that you can achieve using only these devices. The gain can be inverting or non-inverting. Both draw the circuit schematic and provide the value of the gain.

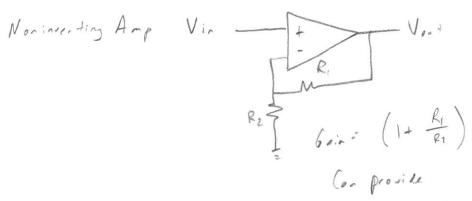


With these 3 circuit elements, the two major possible circuits

Inverting Amp Vir W F. Vo. + Gain = - RZ

Gold provide

[Gain ] = 10



Noninverting Arp

PROBLEM 5 (20 Points)

For the following circuit, determine the output voltage if  $V_{in}=1V$ . (The value of  $V_{supply}$  is coming from a higher voltage supply, and its value is not important).

$$V_{\text{in}} = V_{\text{out}}$$

$$V_{\text{supply}} = V_{\text{out}}$$

$$\frac{V_{1}-V_{-}}{R_{1}} + \frac{V_{0}+V_{-}}{R_{2}} = 0$$

$$V_{0}+\frac{2}{R_{1}} - \frac{2}{R_{1}} - V_{1} + \left(1 + \frac{R_{2}}{R_{1}}\right)V_{-}$$

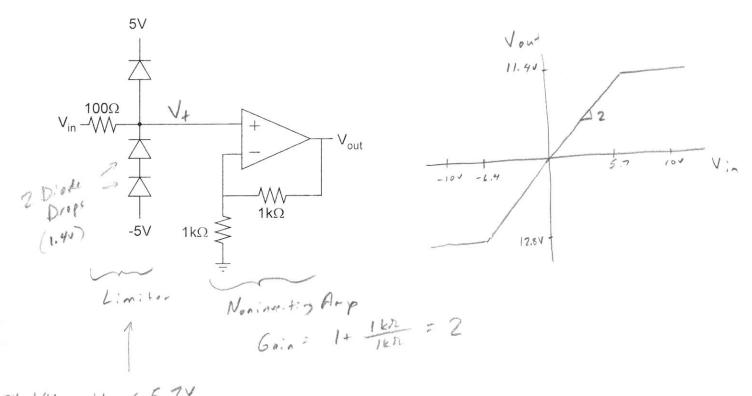
$$V_{0}+\frac{10kh}{20kh} \left(1V\right) + \left(1.5\right)\left(1V\right)$$

$$V_{0}+\frac{1}{20kh} - \frac{10kh}{20kh} \left(1V\right) + \frac{1.5V}{1.5V} = \frac{1}{1}V$$

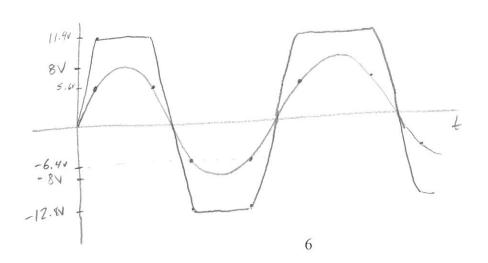
(20 Points)

Sketch the  $V_{\text{out}}$  vs.  $V_{\text{in}}$  transfer function of the following circuit. ( $V_{\text{out}}$  on the y-axis and  $V_{\text{in}}$  on the x-axis.) Let  $V_{in}$  be limited to -10V  $\leq\!\!Vin\!\!\leq\!\!10V.$ 

Extra Credit (5 Points) – Sketch Vout in response to  $Vin=(8V)\sin(2\pi t)$ .



-54-1.40 EV+ 55.70 -6.40 EV+ 55.70 : The input of the noninverting onp is restricted to between -6.44 and 5.74



(5 Points)

In class, we discussed two reverse-bias breakdown mechanisms in diodes. Choose one of these two breakdown mechanism and describe what physically happens. (Figures may help.)

See discussion from class